

Response:

Applicant hereby elects species I (figures 6-14) in response to the above restriction requirement. The 5 claims readable upon the elected species are claims 1-17. No new claims are added.

2. Request for reconsideration of the restriction requirement per 37 CFR 1.143.

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Applicant believes that the present application does not need an election. Since species I (defined by claims 1-17) of the present application discloses a method for forming a self-aligned LTPS TFT, and 15 species II (defined by claims 18-32) of the present application also discloses a method for forming a self-aligned LTPS TFT, both species I and species II disclose a method for forming a self-aligned LTPS TFT. In addition, the characteristic of both species I and 20 species II is to utilize the conductive layer (gate) and the patterned photo resist layer as a hard mask to perform two self-aligned implantation processes. Though species I utilizes a trimming process to change the dimensions of the gaps alongside the gate, while

species II utilizes an isotropic etching process to change the dimensions of the gaps alongside the gates, the spirit of both species I and species II lie in forming the source, the drain, and the lightly doped 5 drains in a self-aligned way.

Therefore, the applicant believes that species I and species II of the present application should be grouped together and should not be patentably distinct.

10 Reconsideration over claims 18-32 is hereby requested.

Sincerely yours,

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Winston Hsu

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Winston Hsu, Patent Agent No.41,526

P.O. BOX 506

Merrifield, VA 22116

20 U.S.A.

e-mail:patent.service@naipo.com.tw

(Please contact me by e-mail if you need a telephone communication and I will return your call promptly.)